

WHAT IS CLAIMED IS:

1. A semiconductor light-emitting device, comprising:
  - a lead frame having a main surface in which a first region and a second region extending along the periphery of said first region are defined;
  - a semiconductor light-emitting element provided at said first region;
  - 5 a first resin member having a first reflectivity with respect to light emitted from said semiconductor light-emitting element and provided at said first region to completely cover said semiconductor light-emitting element; and
  - a second resin member having a second reflectivity greater than
  - 10 said first reflectivity with respect to the light emitted from said semiconductor light-emitting element and provided at said second region to surround said semiconductor light-emitting element; wherein
  - said first resin member includes a first top surface, and
  - said second resin member includes a second top surface that is
  - 15 provided at a position where a distance from said main surface is greater than a distance from said main surface to said first top surface, and an inner wall that is provided on a side where said semiconductor light-emitting element is located and extends in a direction away from said main surface to reach said second top surface.
2. The semiconductor light-emitting device according to claim 1, further comprising a metallic wire having one end connected to said semiconductor light-emitting element and another end connected to said main surface, and said first resin member is provided to completely cover
- 5 said metallic wire.
3. The semiconductor light-emitting device according to claim 2, wherein said one end is formed in a line shape, and said another end is formed in a ball shape.
4. The semiconductor light-emitting device according to claim 2,

wherein said one end is provided with a ball-shaped metal to sandwich said metallic wire between the ball-shaped metal and said semiconductor light-emitting element.

5        5. The semiconductor light-emitting device according to claim 1, comprising three said semiconductor light-emitting elements emitting light of red, blue and green, respectively, and three said lead frames spaced apart from each other and provided with respective said three semiconductor light-emitting elements, said lead frames extending in different directions from each other.

5        6. The semiconductor light-emitting device according to claim 5, wherein areas of said main surfaces of said lead frames provided with said semiconductor light-emitting elements emitting the light of blue and green, respectively, are each greater than an area of said main surface of said lead frame provided with said semiconductor light-emitting element emitting the light of red.

7. The semiconductor light-emitting device according to claim 1, wherein said lead frame includes portions separated by a slit-shaped groove, and said portions are formed thinner than the other portion of said lead frame.

8. The semiconductor light-emitting device according to claim 1, wherein said lead frame is formed in a plate shape extending in one plane.

5        9. The semiconductor light-emitting device according to claim 8, wherein said lead frame includes a first depression that is formed at an opposite surface with respect to said main surface and filled with a resin, and terminal portions to be electrically connected to a mounting board are provided on said opposite surface, on respective sides of said first depression.

10. The semiconductor light-emitting device according to claim 1, wherein said lead frame includes a second depression formed at said first region, and said semiconductor light-emitting element is provided in said second depression.

11. The semiconductor light-emitting device according to claim 1, wherein said lead frame is formed of a metal having a heat conductivity of not lower than 300 W/mK and not greater than 400 W/mK.

12. The semiconductor light-emitting device according to claim 1, wherein said second resin member is formed such that an area of a shape defined by said inner wall in a plane parallel to said main surface increases with an increase of a distance from said main surface.

13. The semiconductor light-emitting device according to claim 1, wherein a shape defined by said inner wall in a plane parallel to said main surface is one of circle, ellipse and polygon.

14. The semiconductor light-emitting device according to claim 1, wherein

said lead frame includes a lead terminal projecting from the periphery of said main surface and extending in a prescribed direction, and  
5 said lead terminal has a tip end portion having an end surface formed at a tip end extending in said prescribed direction, and a base portion located between the periphery of said main surface and said tip end portion, and

said lead terminal is formed such that an area of said end surface is smaller than a cross sectional area of said base portion in a plane parallel  
10 to said end surface.

15. The semiconductor light-emitting device according to claim 14, wherein said lead terminal has a first width at said base portion and a second width smaller than said first width at said tip end portion.

16. The semiconductor light-emitting device according to claim 14, wherein said end surface corresponds to a cut surface formed by a prescribed cutting tool.

17. A manufacturing method of the semiconductor light-emitting device recited in claim 16, comprising the steps of:

preparing a lead frame base member having a plurality of said semiconductor light-emitting devices formed thereon; and

5 cutting the plurality of said semiconductor light-emitting devices out of said lead frame base member by cutting said lead frame base member at said tip end portions.

18. An electronic image pickup device, comprising the semiconductor light-emitting device recited in claim 1.

19. The electronic image pickup device according to claim 18, wherein when a reference plane of a rectangular shape is provided at a prescribed distance from said semiconductor light-emitting device, luminance at each corner of said reference plane irradiated with the light  
5 from said semiconductor light-emitting device is not less than 50% of luminance at the center of said reference plane.